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TYPE : 6PT2006N1T\*\*

CHIP SIZE	0.23 * 0.23 mm
WAFER SIZE	6 inch
POSSIBLE DIE PER WAFER	290,000 pcs

Maximum Ratings(Ta=25°C)

Characteristics	Symbol	Ratings	Unit
Drain-source voltage	VDSS	50	V
Gate-source voltage	VGSS	±8	V
Drain Current (DC)	ID	0.05	A

\* For Reference

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT				CONDITIONS
		MIN.	Typ	MAX.	UNIT	
1	IGSS			5	uA	VGS= ±8.0V VDS= 0V
2	IDSS			500	nA	VDS= 50V VGS= 0V
3	BVDSS	53			V	ID= 1mA
4	VGS(off)	0.4		1.3	V	ID= 100uA VDS= 10V
5	Ron 1		6	7.8	Ω	ID= 50mA VGS= 4.0V
6	Ron 2		7	9.9	Ω	ID= 30mA VGS= 2.5V
7	Ron 3		10.5	20.0	Ω	ID= 10mA VGS= 1.5V
8	VSD			1.2	V	IS= 100mA

※ Built-in ZD between Gate and Source. ESD Protected (350V)

TENTATIVE

NOTE: